## **SKET 330**



# SEMIPACK<sup>®</sup> 4

## **Thyristor Modules**

#### **SKET 330**

#### **Features**

- Heat transfer through aluminium nitride ceramic isolated metal baseplate
- Precious metal pressure contacts for high reliability
- · Thyristor with amplifying gate
- UL recognized, file no. E 63 532

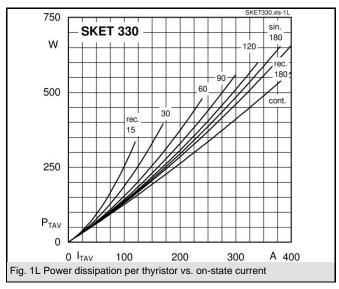
### **Typical Applications**

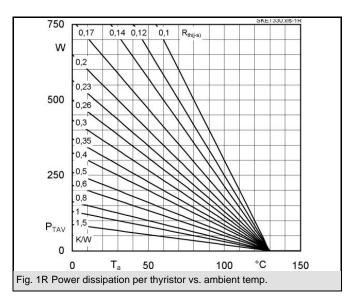
- DC motor control (e. g. for machine tools)
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)
- 1) See the assembly instructions
- 2) The screws must be lubricated

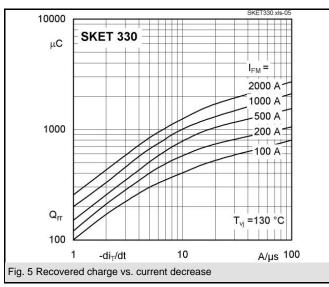
V <sub>RSM</sub>	$V_{RRM}, V_{DRM}$	I <sub>TRMS</sub> = 600 A (maximum value for continuous operation)		
V	V	I <sub>TAV</sub> = 330 A (sin. 180; T <sub>c</sub> = 78 °C)		
900	800	SKET 330/08E		
1300	1200	SKET 330/12E		
1500	1400	SKET 330/14E		
1700	1600	SKET 330/16E		
1900	1800	SKET 330/18E		
2100	2000	SKET 330/20E		
2300	2200	SKET 330/22E		

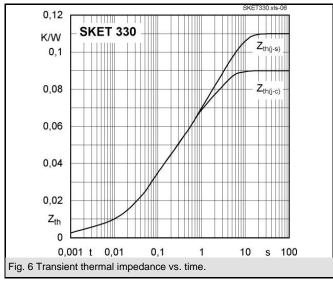
Symbol	Conditions	Values	Units
I <sub>TAV</sub>	sin. 180; T <sub>c</sub> = 85 (100) °C;	295 (210 )	Α
I <sub>D</sub>	P16/300F; T <sub>a</sub> = 35 °C; B2 / B6	530 / 665	Α
I <sub>RMS</sub>	P16/400F; T <sub>a</sub> = 35 °C; W1 / W3	685 / 3 * 550	Α
I <sub>TSM</sub>	T <sub>vi</sub> = 25 °C; 10 ms	9000	Α
	$T_{vj}^{3}$ = 130 °C; 10 ms	8000	Α
i²t	T <sub>vj</sub> = 25 °C; 8,3 10 ms	405000	A²s
	T <sub>vj</sub> = 130 °C; 8,3 10 ms	320000	A²s
$V_T$	T <sub>vj</sub> = 25 °C; I <sub>T</sub> = 1500 A	max. 2,05	V
$V_{T(TO)}$	T <sub>vj</sub> = 130 °C	max. 1,2	V
r <sub>T</sub>	T <sub>vj</sub> = 130 °C	max. 0,55	mΩ
$I_{DD}; I_{RD}$	$T_{vj}$ = 130 °C; $V_{RD}$ = $V_{RRM}$ ; $V_{DD}$ = $V_{DRM}$	max. 200	mA
t <sub>gd</sub>	$T_{vj} = 25 ^{\circ}\text{C}; I_{G} = 1 \text{A}; di_{G}/dt = 1 \text{A/}\mu\text{s}$	1	μs
t <sub>gr</sub>	$V_{\rm D} = 0.67 * V_{\rm DRM}$	2	μs
(di/dt) <sub>cr</sub>	T <sub>vj</sub> = 130 °C	max. 125	A/µs
(dv/dt) <sub>cr</sub>	T <sub>vj</sub> = 130 °C	max. 1000	V/µs
$t_q$	$T_{vj} = 130 ^{\circ}\text{C}$	150 200	μs
I <sub>H</sub>	$T_{vj} = 25 ^{\circ}\text{C}$ ; typ. / max.	150 / 500	mA
IL	$T_{vj}$ = 25 °C; $R_G$ = 33 $\Omega$ ; typ. / max.	500 / 2000	mA
V <sub>GT</sub>	T <sub>vj</sub> = 25 °C; d.c.	min. 3	V
I <sub>GT</sub>	$T_{vj} = 25 ^{\circ}\text{C}; \text{d.c.}$	min. 200	mA
$V_{GD}$	$T_{vj} = 130 ^{\circ}\text{C}; \text{d.c.}$	max. 0,25	V
$I_{GD}$	$T_{vj} = 130 ^{\circ}\text{C};  \text{d.c.}$	max. 10	mA
R <sub>th(j-c)</sub>	cont.	0,09	K/W
R <sub>th(j-c)</sub>	sin. 180	0,095	K/W
R <sub>th(j-c)</sub>	rec. 120	0,11	K/W
$R_{th(c-s)}$		0,02	K/W
$T_{vj}$		- 40 + 130	°C
$T_{stg}$		- 40 + 130	°C
V <sub>isol</sub>	a. c. 50 Hz; r.m.s.; 1s / 1 min.	3600 / 3000	V~
$M_s$	to heatsink	5 ± 15 % <sup>1)</sup>	Nm
$M_t$	to terminal	17 ± 15 % <sup>2)</sup>	Nm
а		5 * 9,81	m/s²
m	approx.	940	g
Case		A 36	

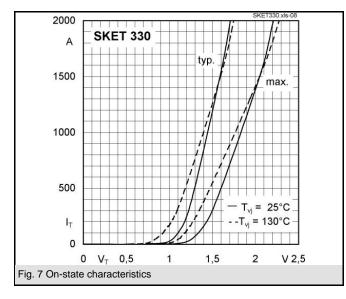


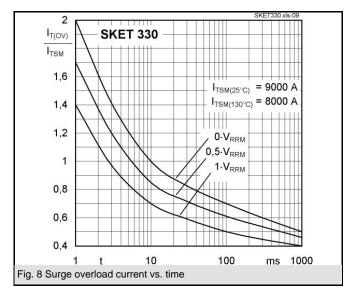


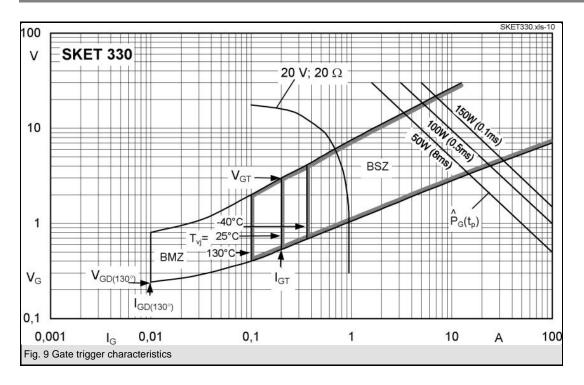


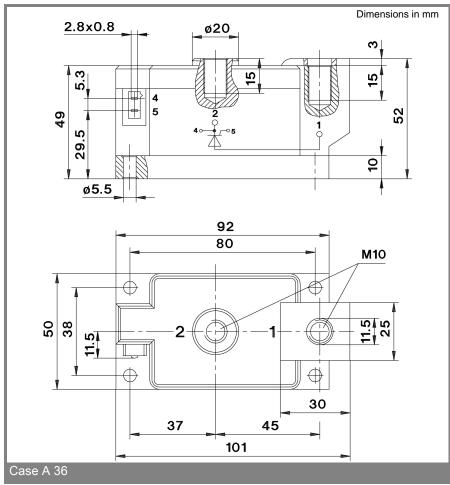












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